

**In the Abstract**

Please amend the Abstract as indicated. A replacement Abstract, provided on a separate sheet, is attached hereto.

A high voltage device comprising a substrate of a first type, [[a]] first and second [[well]] wells respectively of the first type and a second type in the substrate, a gate formed on the substrate, [[a]]first and second doped region regions both of the second type, respectively formed in the first and second [[well]] wells and both sides of the gate, and a third doped region of the first type in the first well and adjacent to the first doped region.